Growth and material properties of ZnTe on GaAs, InP, InAs and GaSb (0 0 1) substrates for electronic and optoelectronic device applications

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1. Introduction

ZnTe is a direct-band semiconductor with a bandgap of 2.26 eV (549 nm). It is considered to be suitable for various optoelectronic devices such as pure-green light-emitting diodes, green laser diodes, UV-green photodetectors, and multijunction solar cells [1,2]. Although pure-green ZnTe LEDs have been successfully demonstrated on ZnTe substrates [3,4], one of the big obstacles in making them commercially applicable is the high cost and small size of current ZnTe bulk substrates. It is therefore highly desirable to have larger wafer size ZnTe virtual substrates. Thin ZnTe grown on Si has also been used for ZnCdTe virtual substrates for HgCdTe infrared detectors [5–7]. However, due to the large lattice mismatch between ZnTe and Si, such thin ZnTe layers grown on Si have high misfit dislocation density. Since ZnTe has a lattice constant of 6.1 Å, which is nearly lattice-matched to 6.1 Å III–V substrates, such as GaAs with a mismatch of only 0.13%, and InAs with a mismatch of 0.75%, ZnTe grown on these substrates is expected to have low density of misfit dislocations. Moreover, GaAs and InP are also good substrate candidates for electronic devices and infrared photo-detectors due to their semi-insulating properties and transparency in the infrared range [8]. Thus, the ability to achieve high quality ZnTe epitaxial growth on these different substrates, and the possibility to reduce the overall material cost, are very important considerations not only for ZnTe related devices, but also for electronic and optoelectronic device applications based on these 6.1 Å compound semiconductors that can be grown lattice matched to ZnTe virtual substrate.

In this paper, we propose the use of thick ZnTe epilayers grown on III–V substrates as low-cost virtual substrates. A set of ZnTe samples has been grown on GaAs, InP, InAs and GaSb (0 0 1) substrates using molecular beam epitaxy (MBE), and the material properties of the ZnTe films have been investigated. During MBE growth, in situ reflection high energy electron diffraction (RHEED) is used for growth monitoring and optimization. X-ray diffraction (XRD) measurements are performed to analyze the strain of the ZnTe epilayers and high resolution electron microscopy (HREM) is used to study the structural properties of the ZnTe epilayers, especially misfit dislocations at the interface. Photoluminescence is also applied to characterize the optical properties of the ZnTe epilayers. Growth of high-quality ZnTe samples is successfully demonstrated on all four substrates.

2. Experiments

The epitaxial growth was carried out using an MBE system consisting of III–V and II–VI chambers connected with an ultra-high-vacuum transfer module. The vacuum of the transfer chamber was typically about 5 × 10⁻¹⁰ Torr, which prevented any significant contamination during sample transfer. For growth of the samples, the
substrates were firstly deoxidized in the III–V chamber, followed by growth of III–V semiconductor buffer layers. The substrate temperatures were measured with a thermocouple on the back of the substrate holder. The growth orientation for all samples was (0 0 1). After the samples were cooled down to room temperature, they were transferred to the II–VI chamber where the ZnTe layers were grown. The substrate temperature during ZnTe growth was 330 °C. The growth parameters for the samples described in this paper are summarized in Table 1.

During growth, the beam equivalent pressure (BEP) ratios of Zn to Te were adjusted to optimize the growth conditions by monitoring the surface reconstructions using RHEED. The RHEED patterns for ZnTe samples appeared to be similar regardless of the specific III–V substrate used for the growths. As an example, RHEED patterns for ZnTe grown on InAs (0 0 1) substrate are shown in Fig. 1. A (2 × 4) reconstruction of the InAs surface is visible before growth of the ZnTe layer was commenced. At the beginning of ZnTe growth, the RHEED pattern showed a spotty and weakly defined pattern, indicating a transition from the (2 × 4) to the (1 × 2) surface reconstruction. The transition time was in the range of 10 s to 1 min. After the transition of the surface reconstruction, the typical ZnTe (1 × 2) pattern appeared and stayed bright and streaky throughout the rest of the ZnTe growth.

The cross-sectional HREM samples were prepared using mechanical polishing and dimpling followed by ion-beam thinning. Liquid nitrogen and low energy (2.5–3 keV) ion beams were used to avoid any thermal damage. Images were recorded using a JEM-4000EX HREM operated at 400 keV with a structural resolution of ~1.7 Å. The high-resolution XRD rocking curve measurements were performed using a PANalytical X’Pert PRO MRD X-ray diffractometer with multi-crystal monochromator. The copper Kα1 line (1.54 Å) was used as the incident beam. For characterization of optical properties, temperature-dependent PL measurements were carried out using the 488 nm line of an Argon ion laser for excitation and a high-resolution grating spectrometer equipped with a photomultiplier for detection.

### Table 1
**Growth parameters for the ZnTe samples.**

<table>
<thead>
<tr>
<th>Sample no.</th>
<th>Substrate</th>
<th>Zn:Te BEP ratio</th>
<th>Growth rate (nm/s)</th>
<th>Lattice mismatch (%)</th>
<th>ZnTe layer thickness (µm)</th>
</tr>
</thead>
<tbody>
<tr>
<td>I</td>
<td>GaAs</td>
<td>1.2:1</td>
<td>0.30</td>
<td>7.30</td>
<td>2.5</td>
</tr>
<tr>
<td>II</td>
<td>InP</td>
<td>1.2:1</td>
<td>0.28</td>
<td>3.85</td>
<td>2.3</td>
</tr>
<tr>
<td>III</td>
<td>InAs</td>
<td>1.2:1</td>
<td>0.30</td>
<td>0.75</td>
<td>2.4</td>
</tr>
<tr>
<td>IV</td>
<td>GaSb</td>
<td>1.2:1</td>
<td>0.31</td>
<td>0.13</td>
<td>2.5</td>
</tr>
</tbody>
</table>

### 3. Results and discussion

After completion of growth, high-resolution XRD measurements are performed on all samples in the vicinity of the (0 0 4) and (3 1 1) diffraction peaks of the substrates. These XRD patterns show two clear diffraction peaks coming from both the ZnTe epilayer and the particular substrate material. Fig. 2 compares the XRD patterns of ZnTe epilayers grown on the various substrates. The full-width at half-maximum (FWHM) of the ZnTe epilayers are in the range of 33–60 arcsec, indicating that the thick ZnTe layers grown on all four substrates are of high quality.

Due to the different lattice constants between ZnTe and the various III–V (0 0 1) substrates, strain occurs in the ZnTe epilayers during growth, making the lattice constants of the ZnTe epilayers different from that of bulk ZnTe. The room temperature lattice constants of ZnTe along the growth direction (a₁) and in the layer plane (a₃) are calculated from the XRD results obtained for the (0 0 4) and (3 1 1) reflections, using Bragg’s Law and the following equations:

\[
\begin{align*}
\sin \theta_{\text{epi}} &= \frac{\sin \theta_{\text{sub}}}{a_\text{e}} \quad \text{(1)} \\
\frac{h^2}{a_\text{e}^2} + \frac{k^2}{a_\text{e}^2} + \frac{l^2}{a_\text{e}^2} &= \left(\frac{2\sin \theta_{\text{epi}}}{\lambda}\right)^2 \quad \text{(2)}
\end{align*}
\]

where \( a_\text{e} \) is the lattice constant for the substrate, \( \theta_\text{e} \) and \( \theta_{\text{epi}} \) are the angles for the diffraction peaks of the substrates and the ZnTe epilayers, respectively, and \( h, k, \) and \( l \) are the Miller indices of the diffraction planes.

The lattice constants measured for ZnTe grown on various substrates are summarized in Table 2. Compared with the reported lattice constant of bulk ZnTe at room temperature (6.1037 Å) [9], the \( a_\text{e} \) lattice parameters of all ZnTe epilayers are smaller, which indicates residual tensile strain (parallel to the surface). The major factors related to this residual tensile strain are the lattice constants, thermal expansion coefficients, and growth temperatures. The lattice constants and thermal expansion coefficients for bulk GaAs, InP, InAs, GaSb and ZnTe are listed in Table 3 [9]. ZnTe has a larger bulk lattice constant than all of the substrate materials (GaAs, InP, InAs and GaSb) used in this study. Therefore, compressive strain due to this lattice mismatch is induced during the initial ZnTe growth at the growth temperature. Such compressive strain can be easily measured when the ZnTe layer is thin (~110 nm), as reported in our previous study [2]. However, when the ZnTe layers are grown beyond a certain critical thickness, the strain due to the lattice mismatch between ZnTe and the specific substrate becomes fully relaxed at the growth temperature. For example, it has been reported that the critical thickness for ZnTe grown on GaAs (0 0 1) substrate by MBE is about 15 nm, compared with 180 nm for ZnTe grown on GaSb substrate using organometallic vapor phase epitaxy (OMVPE) [10,11]. Therefore, for ZnTe thicknesses in the range of 2.3–2.5 µm, it is reasonable to assume that the compressive strain due to lattice mismatch is fully relaxed in the ZnTe epilayers at the growth temperature. Moreover, ZnTe has a larger thermal expansion coefficient (8.33 × 10⁻⁶ K⁻¹) than that of all of the substrate materials. Thus, when the samples are cooled down to room temperature after the growth, the thermal shrinkage of the ZnTe epilayers is greater than for the substrates. Accordingly, tensile strain occurs in the ZnTe epilayer.

The misfit dislocations present at the various ZnTe/substrate interfaces are studied using HREM. As visible in Fig. 3(a), low magnification images of the ZnTe/GaAs sample show a high density of misfit dislocations near the interface, which is attributed to the large lattice mismatch of 7.3% between ZnTe and GaAs. It is also apparent that the dislocation density becomes much less as the
ZnTe thickness increases. The high magnification image in Fig. 3(b) shows that there are pseudo-periodic dislocations present at the ZnTe/GaAs interface. Burgers’ circuits drawn directly on high magnification images indicate that 39% of these dislocations are Lomer edge dislocations, with the remainder being 601 partial dislocations. As shown in Fig. 3(c), the Burgers vector of the Lomer dislocation labeled with an arrow corresponds to one-half lattice spacing along the [1 1 0] direction, i.e. a0/2 [1 1 0].

PL measurements are carried out to study the optical properties of the ZnTe samples. The PL spectra of all the ZnTe samples measured at 300 K are shown in Fig. 4(a). Regardless of the substrates, all the PL peaks are at 2.26 eV. The PL emission from ZnTe epilayer grown on GaSb has the strongest intensity, which is attributed to the minimal defect density in the epilayer due to the smallest lattice mismatch of 0.13% between ZnTe and GaSb. Similarly, the sample of ZnTe grown on InAs with a lattice mismatch of 0.75% shows much stronger PL intensity than that of the other two ZnTe samples grown on InP and GaAs substrates, which have larger lattice mismatches of 3.85% and 7.30%, respectively. Temperature-dependent PL spectra of ZnTe grown on GaAs are shown in Fig. 4(b). As temperature increases, the PL peak shows red-shift due to decrease in the bandgap energy, and the FWHM of the PL spectrum becomes broader as expected. In addition, a broad PL emission below bandgap energy is observed at 80 K. This emission is attributed to defects related optical transitions, and more detailed study will be published separately.

4. Summary

The use of thick epitaxial grown ZnTe as a low-cost virtual substrate is proposed for various device applications and high-quality thick ZnTe layers are successfully grown on various GaAs, InP, InAs and GaSb (0 0 1) substrates using MBE. High-resolution XRD results show narrow FWHM (33–60 arcsec) for the ZnTe epilayers grown on all four different substrates. The lattice parameters for ZnTe epilayers along the growth direction (a0) and in the layer plane (a1) are measured and show that residual tensile strains are present in the ZnTe layers due to the difference in thermal expansion coefficients between the epilayers and the substrates. HREM images reveal that Lomer edge dislocations and 601 partial
dislocations are the predominant defects present at the ZnTe/GaAs and ZnTe/InP interfaces. The defect densities in all films become lower as the ZnTe thickness is increased. Strong PL spectra for all the ZnTe samples are observed from 80 to 300 K. The PL peak positions of ZnTe epilayers are at 2.26 eV at room temperature.

Acknowledgments

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References